



**THE DATASHEET OF  
PBSS5160DS,115**



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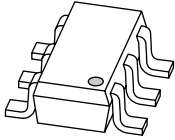
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Kind regards,

Team Nexperia



# PBSS5160DS

60 V, 1 A PNP/PNP low  $V_{CEsat}$  (BISS) transistor

Rev. 03 — 9 October 2008

Product data sheet

## 1. Product profile

### 1.1 General description

PNP/PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor pair in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4160DS.

### 1.2 Features

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- Dual low power switches (e.g. motors, fans)
- Automotive applications

### 1.4 Quick reference data

Table 1. Quick reference data

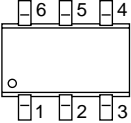
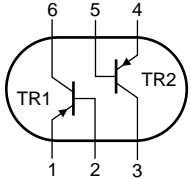
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-60	V
$I_C$	collector current		[1]	-	-1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-2	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -1$ A; $I_B = -100$ mA	[2]	250	330	m $\Omega$

[1] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

[2] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

## 2. Pinning information

**Table 2. Pinning**

Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		

*sym018*

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
PBSS5160DS	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

## 4. Marking

**Table 4. Marking codes**

Type number	Marking code
PBSS5160DS	A5

## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

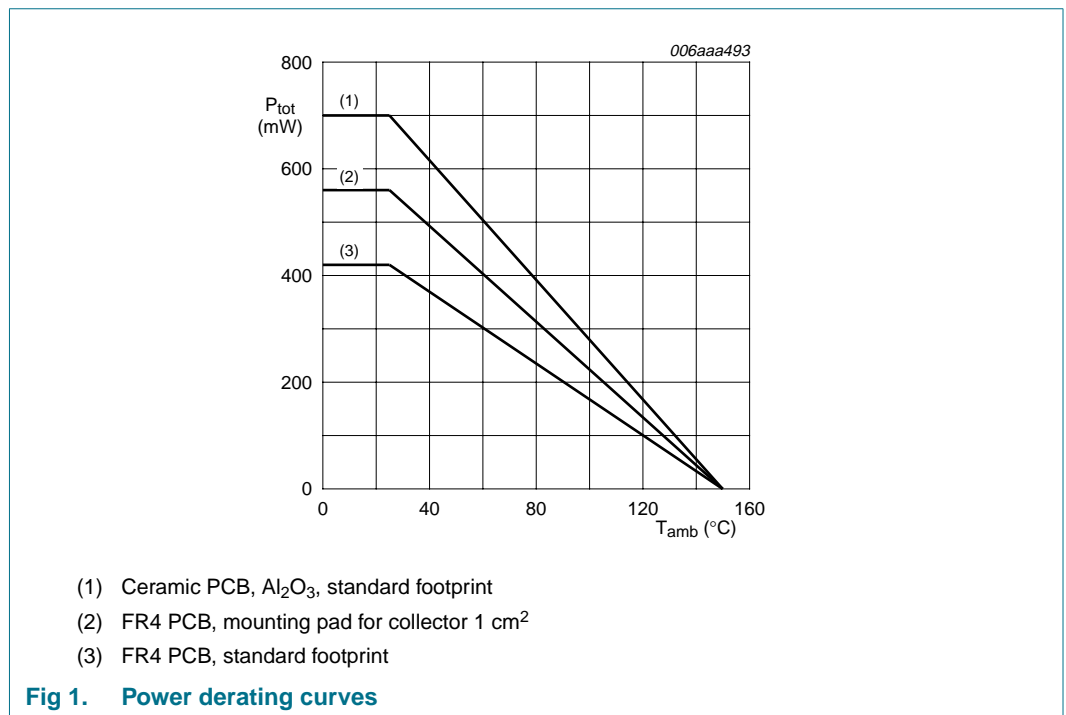
Symbol	Parameter	Conditions	Min	Max	Unit
<b>Per transistor</b>					
$V_{CBO}$	collector-base voltage	open emitter	-	-80	V
$V_{CEO}$	collector-emitter voltage	open base	-	-60	V
$V_{EBO}$	emitter-base voltage	open collector	-	-5	V
$I_C$	collector current		[1]	-0.77	A
			[2]	-0.9	A
			[3]	-1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-2	A
$I_B$	base current		-	-300	mA
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms	-	-1	A

**Table 5. Limiting values ...continued**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	290	mW
			[2]	-	370	mW
			[3]	-	450	mW
<b>Per device</b>						
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	420	mW
			[2]	-	560	mW
			[3]	-	700	mW
$T_j$	junction temperature		-	150	°C	
$T_{amb}$	ambient temperature		-65	+150	°C	
$T_{stg}$	storage temperature		-65	+150	°C	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

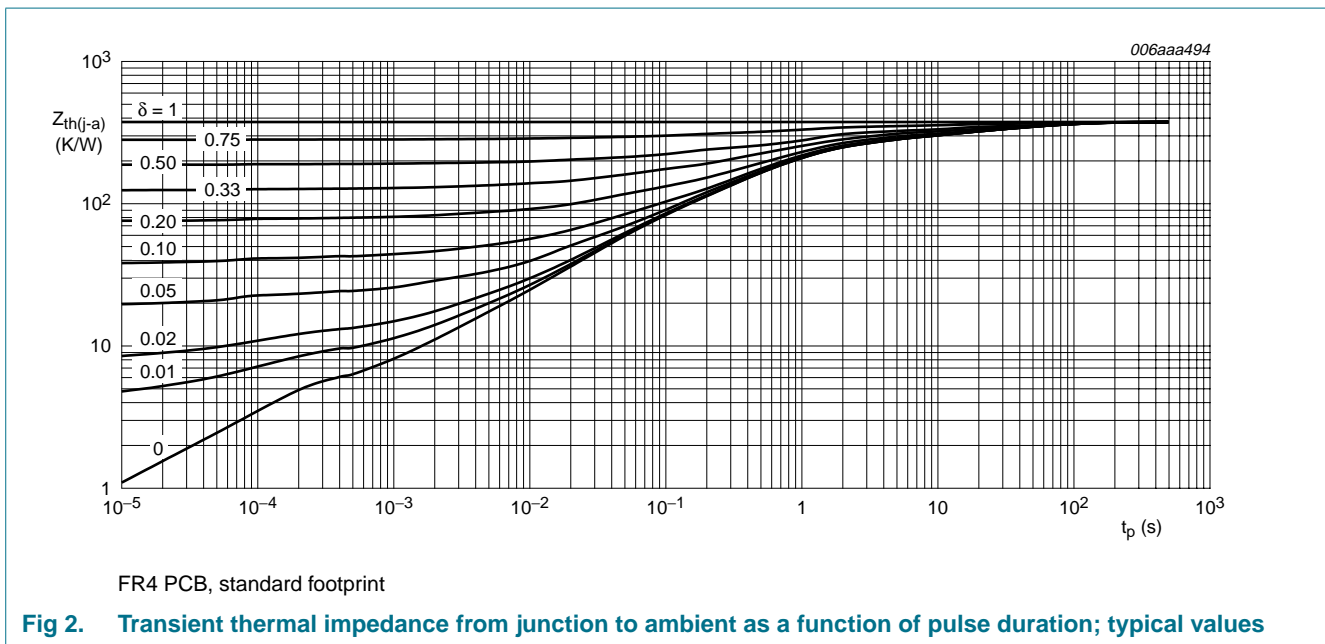


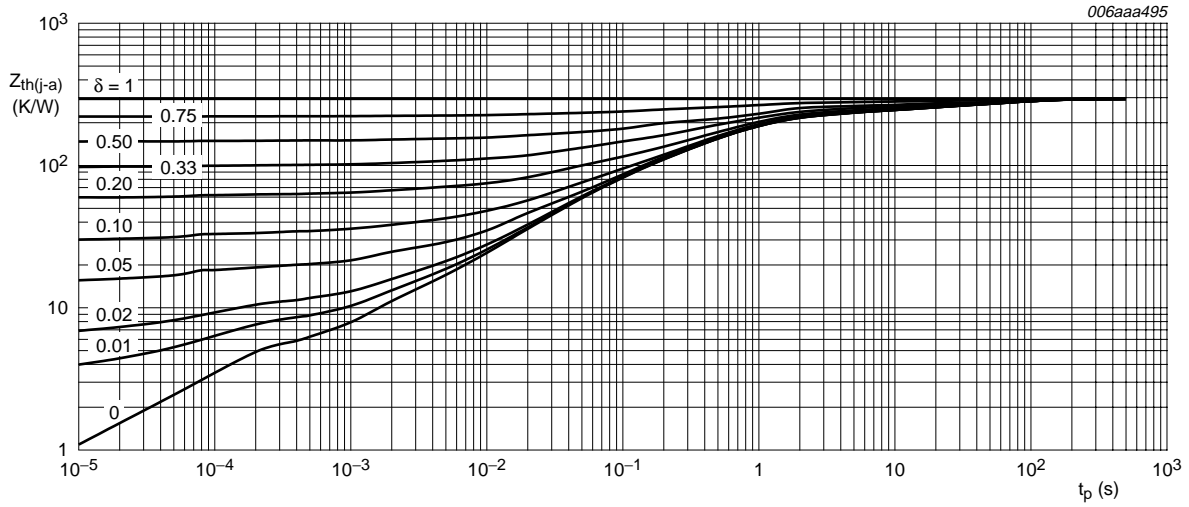
## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Per transistor</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	431	K/W
			[2]	-	-	338	K/W
			[3]	-	-	278	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W	
<b>Per device</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	298	K/W
			[2]	-	-	223	K/W
			[3]	-	-	179	K/W

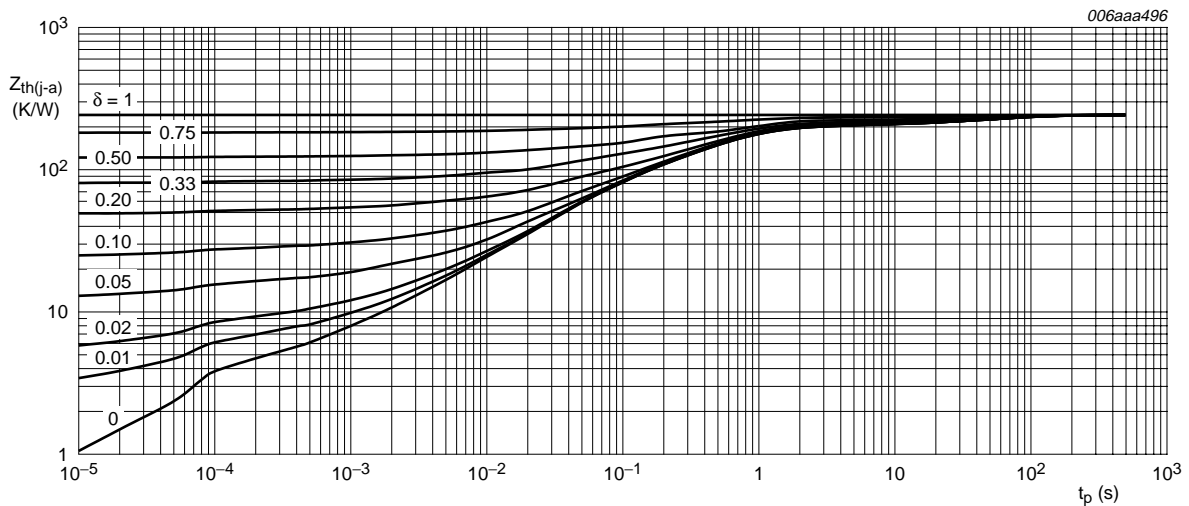
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.





FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

**Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

**Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

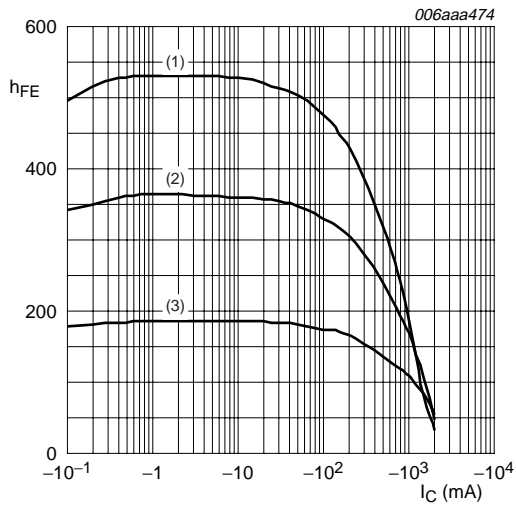
## 7. Characteristics

**Table 7. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

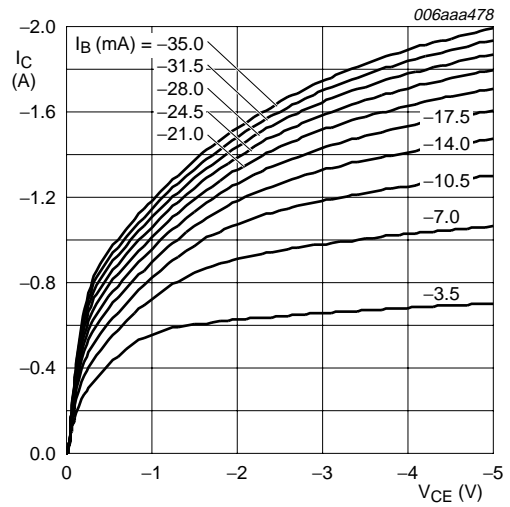
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -60\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
		$V_{CB} = -60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	$\mu\text{A}$
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = -60\text{ V}; V_{BE} = 0\text{ V}$	-	-	-100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	200	350	-	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	[1] 150	250	-	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	[1] 100	160	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	-	-110	-165	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	-	-120	-175	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1] -	-250	-330	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	[1] -	-0.95	-1.1	V
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1] -	250	330	$\text{m}\Omega$
$V_{BEon}$	base-emitter turn-on voltage	$I_C = -1\text{ A}; V_{CE} = -5\text{ V}$	[1] -	-0.82	-0.9	V
$t_d$	delay time	$I_C = -0.5\text{ A}; I_{Bon} = -25\text{ mA}; I_{Boff} = 25\text{ mA}$	-	11	-	ns
$t_r$	rise time		-	30	-	ns
$t_{on}$	turn-on time		-	41	-	ns
$t_s$	storage time		-	205	-	ns
$t_f$	fall time		-	55	-	ns
$t_{off}$	turn-off time		-	260	-	ns
$f_T$	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	150	185	-	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	9	15	pF

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



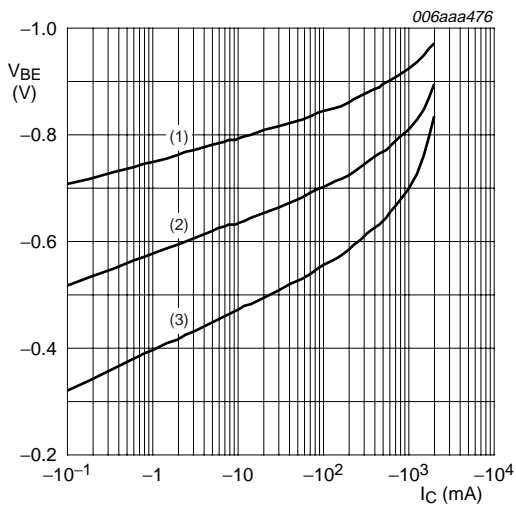
- $V_{CE} = -5 V$
- (1)  $T_{amb} = 100^\circ C$
  - (2)  $T_{amb} = 25^\circ C$
  - (3)  $T_{amb} = -55^\circ C$

**Fig 5. DC current gain as a function of collector current; typical values**



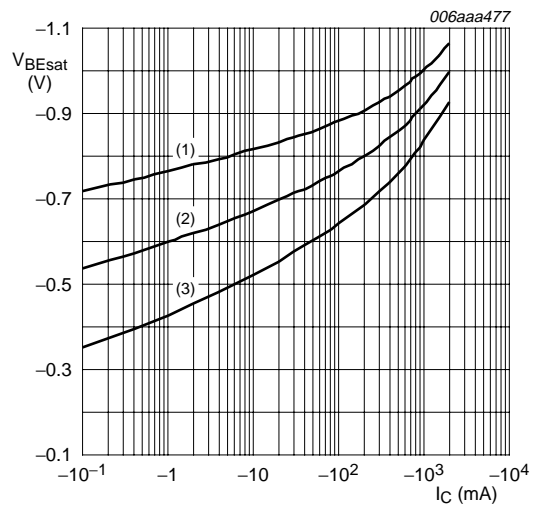
$T_{amb} = 25^\circ C$

**Fig 6. Collector current as a function of collector-emitter voltage; typical values**



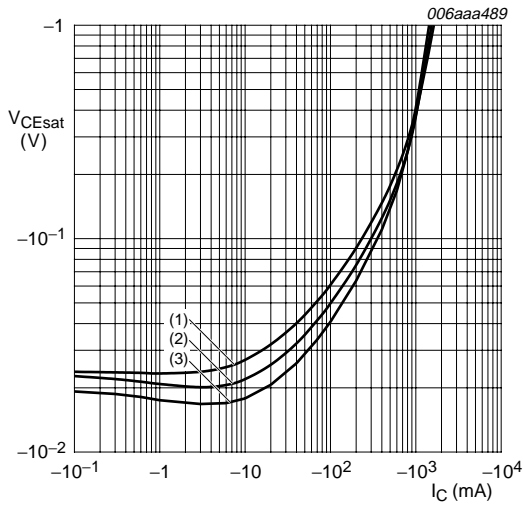
- $V_{CE} = -5 V$
- (1)  $T_{amb} = -55^\circ C$
  - (2)  $T_{amb} = 25^\circ C$
  - (3)  $T_{amb} = 100^\circ C$

**Fig 7. Base-emitter voltage as a function of collector current; typical values**



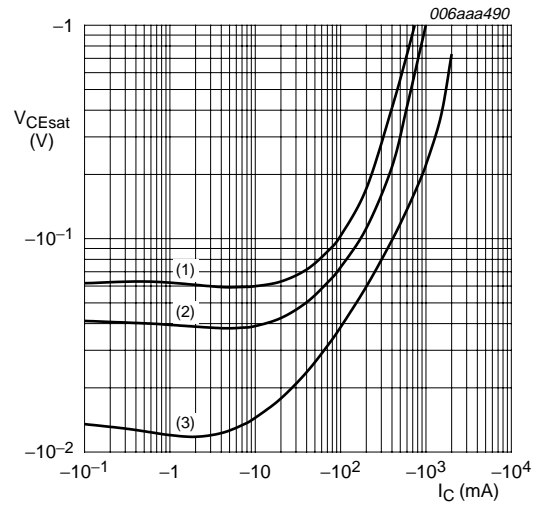
- $I_C/I_B = 20$
- (1)  $T_{amb} = -55^\circ C$
  - (2)  $T_{amb} = 25^\circ C$
  - (3)  $T_{amb} = 100^\circ C$

**Fig 8. Base-emitter saturation voltage as a function of collector current; typical values**



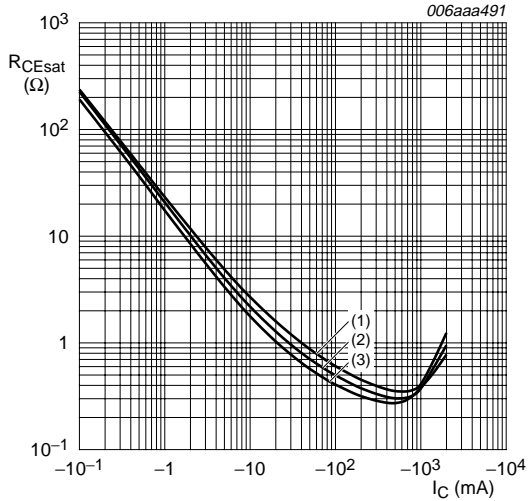
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values**



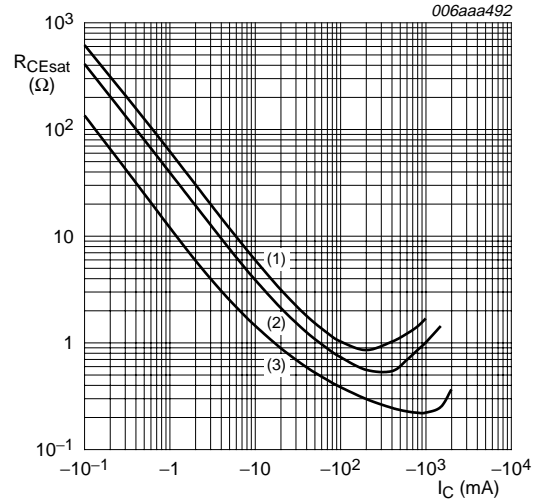
$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

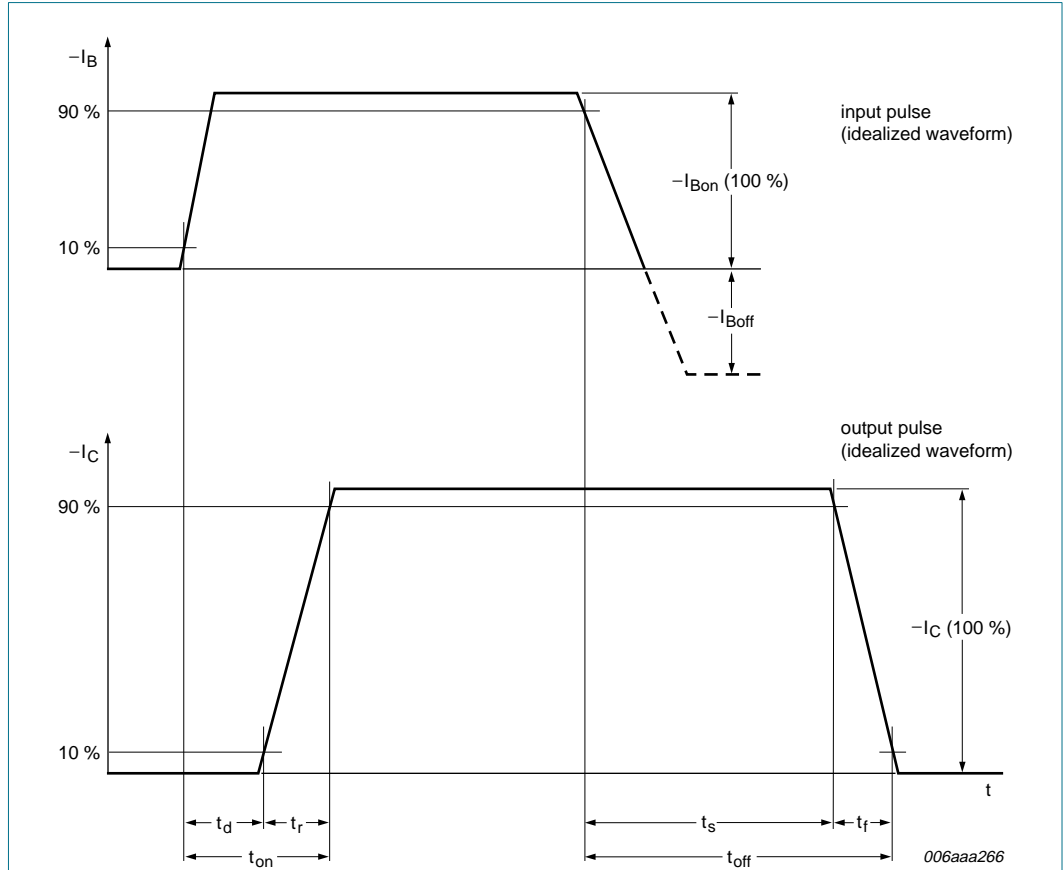
**Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values**



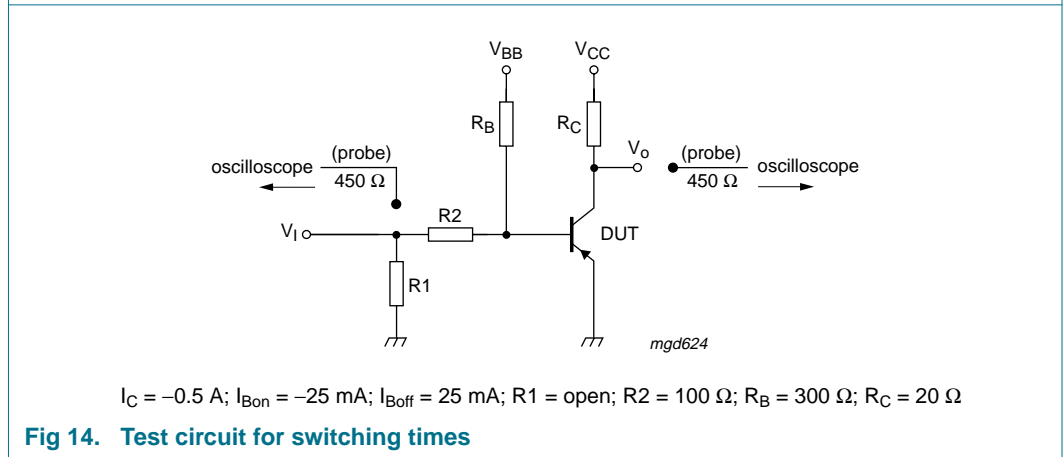
$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values**

**8. Test information**



**Fig 13. BISS transistor switching time definition**



**Fig 14. Test circuit for switching times**

## 9. Package outline

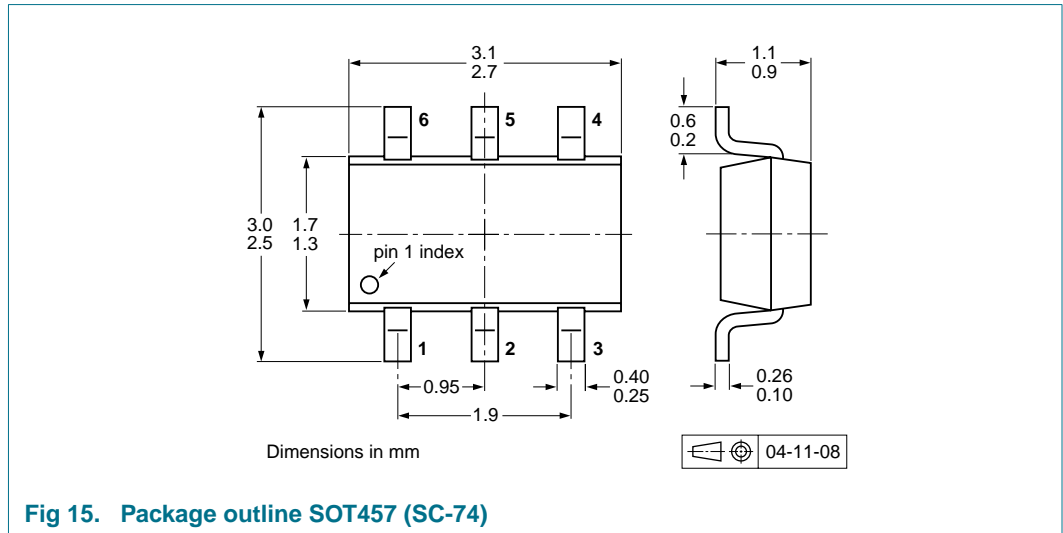


Fig 15. Package outline SOT457 (SC-74)

## 10. Packing information

**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

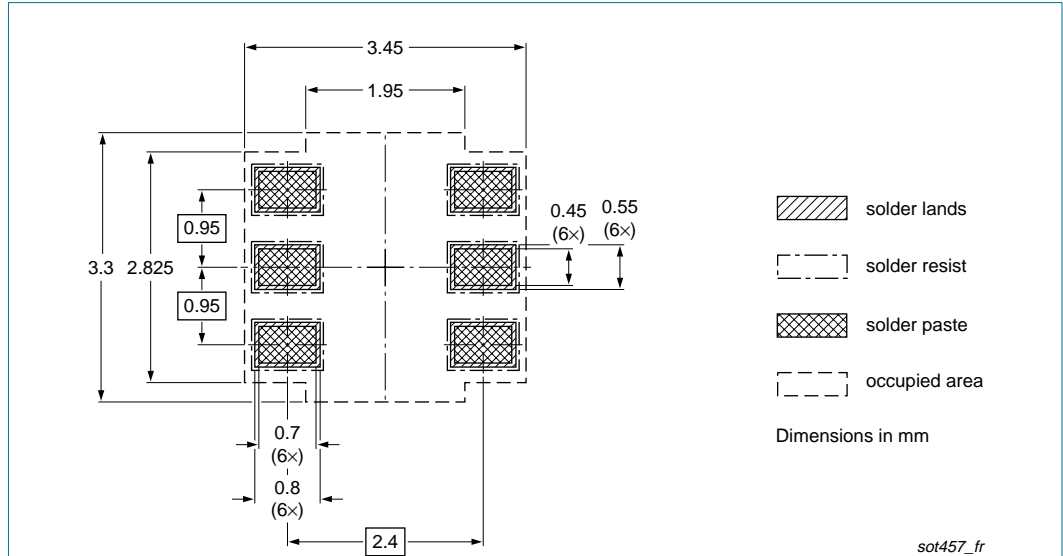
Type number	Package	Description	Packing quantity	
			3000	10000
PBSS5160DS	SOT457	4 mm pitch, 8 mm tape and reel; T1	<sup>[2]</sup> -115	-135
		4 mm pitch, 8 mm tape and reel; T2	<sup>[3]</sup> -125	-165

[1] For further information and the availability of packing methods, see [Section 14](#).

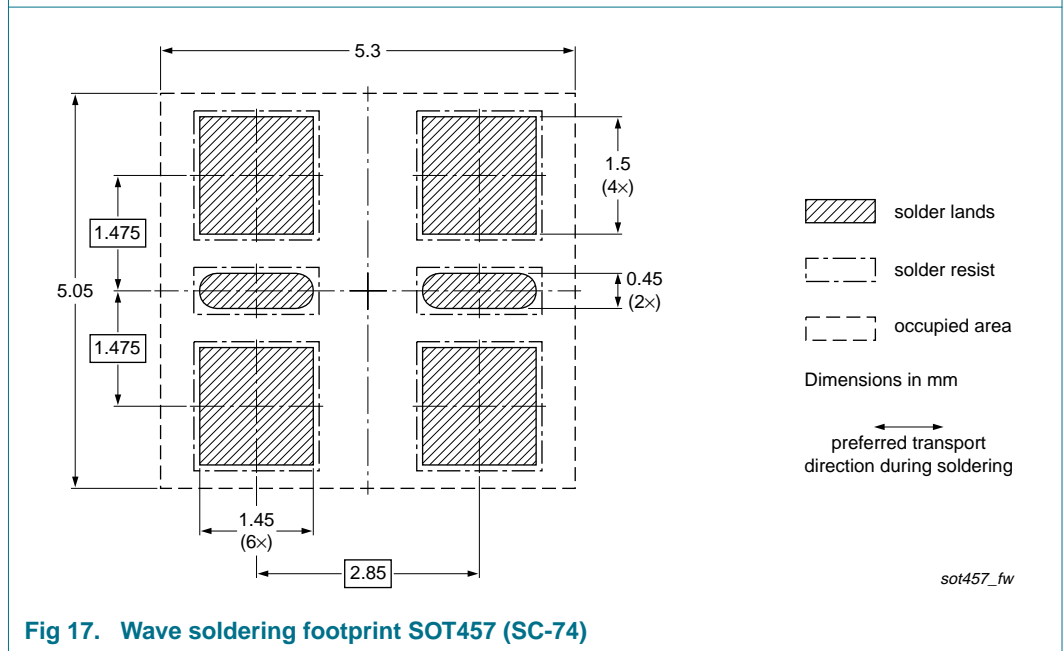
[2] T1: normal taping

[3] T2: reverse taping

**11. Soldering**



**Fig 16. Reflow soldering footprint SOT457 (SC-74)**



**Fig 17. Wave soldering footprint SOT457 (SC-74)**

## 12. Revision history

**Table 9. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5160DS_3	20081009	Product data sheet	-	PBSS5160DS_2
Modifications:		<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• <a href="#">Figure 9</a>: amended</li><li>• <a href="#">Section 13 "Legal information"</a>: updated</li></ul>		
PBSS5160DS_2	20050628	Product data sheet	-	PBSS5160DS_1
PBSS5160DS_1	20040716	Objective data sheet	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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